

2SC3266

NPN Silicon Epitaxial Planar Transistor

for power amplifier and power switching applications.

The transistor is subdivided into three groups, Y, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector to Base Voltage	V_{CBO}	20	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current	I_C	2	A
Power Dissipation	P_{tot}	750	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 3\text{ V}$, $I_C = 500\text{ mA}$ Current Gain Group Y G L	h_{FE}	120	-	240	-
	h_{FE}	200	-	400	-
	h_{FE}	350	-	700	-
Collector Base Cutoff Current at $V_{CB} = 20\text{ V}$	I_{CBO}	-	-	0.1	μA
Emitter Base Cutoff Current at $V_{EB} = 6\text{ V}$	I_{EBO}	-	-	0.1	μA
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	20	-	-	V
Emitter Base Breakdown Voltage at $I_E = 0.1\text{ mA}$	$V_{(BR)EBO}$	6	-	-	V
Collector Emitter Saturation Voltage at $I_C = 2\text{ A}$, $I_B = 0.2\text{ A}$	$V_{CE(sat)}$	-	-	0.8	V
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 0.5\text{ A}$	f_T	-	270	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	14	-	pF



